Docket No. AMENDMENT TRANSMITTAL LETTER M4065.0223/P223 Filing Date Art Unit Application No. Examiner 09/517,314 March 2, 2000 D. Kang 2811 Applicant(s): Chih-chen Cho vention: BACKEND METALLIZATION METHOD AND DEVICE OBTAINED THEREFROM TO THE COMMISSIONER FOR PATENTS Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below. **CLAIMS AS AMENDED** Claims Highest Remaining Number Number **Extra Claims** After Previously Amendment **Present** Rate Paid 0.00 **Total Claims** 23 31 х Independent 0.00 3 4 = х Claims Multiple Dependent Claims (check if applicable) Other fee (please specify): TOTAL ADDITIONAL FEE FOR THIS AMENDMENT: Small Entity

x Large Entity	Small Entity
No additional fee is required for this amend	ment.
Please charge Deposit Account No. A duplicate copy of this sheet is enclosed.	in the amount of \$
A check in the amount of \$	to cover the filing fee is enclosed.
Payment by credit card. Form PTO-2038 is	attached.
The Commissioner is hereby authorized to as described below. A duplicate copy of this	-
x Credit any overpayment.	
x Charge any additional filing or application	processing fees required under 37 CFR 1.16 and 1.17.
Jazo	Dated: September 11, 2002
Thomas J. O'Amico	
Attornov Pea No : 28 371	

Attorney Reg. No.: 28,371

DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 2101 L Street NW

Washington, DC 20037-1526

(202) 828-2232



Docket No.: M4065.0223/P223 (PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Chih-Chen Cho

Application No.: 09/517,314

Filed: March 2, 2000

For: BACKEND METALLIZATION METHOD AND DEVICE OBTAINED THEREFROM

Group Art Unit: 2811

Examiner: Donghee Kang

Paylo

TECHNOLOGY CENTER 2800

PRELIMINARY AMENDMENT

Box Non-Fee Amendment

Commissioner for Patents Washington, DC 20231

Dear Sir:

Prior to continued prosecution, please amend the above-identified U.S. patent application as follows:

In the Claims:

Please amend claims 1, 11, and 25 to read as follows.

1. (Twice Amended) A semiconductor device comprising:

an insulator layer;

a conductive plug positioned within said insulator layer and formed of a

single conductive material

a doped region connected to said conductive plug;

an etch-stop ayer located on said insulator layer and surrounding said plug;

1503828 v1; W8D001!.DOC